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(54) **METHOD FOR FABRICATING
SEMICONDUCTOR DEVICE**

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(57)

ABSTRACT

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A method for fabricating a semiconductor device using an overlay measurement and a semiconductor device fabricated by the method are provided. The method includes forming a lower pattern including a lower overlay key pattern having a first pitch, on a substrate, forming an upper pattern including an upper overlay key pattern having a second pitch different from the first pitch, on the lower pattern, measuring an overlay between the lower overlay key pattern and the upper overlay key pattern, removing the upper overlay key pattern, and after removing the upper overlay key pattern, performing an etching process using the upper pattern as an etching mask.

